

### MT4606

### **Dual N & P-Channel PowerTrench® MOSFET**

#### **General Description**

These dual N- and P-Channel enhancement mode power field effect transistors are produced using MOS-TECH Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state ressitance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

#### **Features**

Q1: N-Channel

$$R_{DS(on)} = 0.028\Omega @ V_{GS} = 10V$$

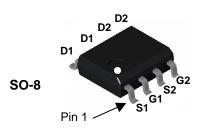
$$R_{DS(on)} = 0.040\Omega$$
 @  $V_{GS} = 4.5V$ 

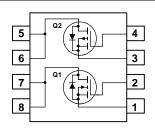
Q2: P-Channel

$$R_{DS(on)} = 0.052\Omega$$
 @  $V_{GS} = -10V$ 

$$R_{DS(on)} = 0.080\Omega$$
 @  $V_{GS} = -4.5V$ 

- Fast switching speed
- High power and handling capability in a widely used surface mount package





### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Q1	Q2	Units	
V <sub>DSS</sub>	Drain-Source Voltage	30	30	V	
V <sub>GSS</sub>	Gate-Source Voltage		±20	±20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	7	-5	Α
	- Pulsed		20	-20	
P <sub>D</sub>	Power Dissipation for Dual Operation	2	W		
	Power Dissipation for Single Operation	1.			
		0			
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Tempera	-55 to	°C		

#### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Package Marking and Ordering Information

-	Device Marking	Device	Reel Size	Tape width	Quantity	
-	MT4606	MT4606	13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Type	Min	Тур	Max	Units
Off Cha	racteristics						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	Q1 Q2	30 -30			V
<u>ΔBV<sub>DSS</sub></u> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 μA, Referenced to 25°C $I_D$ = -250 μA, Referenced to 25°C	Q1 Q2		25 -22		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$	Q1 Q2			1 -1	μА
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	All			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$	All			-100	nA
On Cha	racteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$ $V_{DS} = V_{GS}, I_D = -250 \mu A$	Q1 Q2	1 -1	1.6 -1.7	3 -3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to 25°C $I_D = -250 \mu\text{A}$ , Referenced to 25°C	Q1 Q2		-4.3 4		mV/°C
R <sub>DS(on)</sub> Static	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 7 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 6 \text{ A}$	Q1		21 32 27	28 42 40	mΩ
		$V_{GS} = -10 \text{ V}, I_D = -5 \text{ A}$ $V_{GS} = -10 \text{ V}, I_D = -5 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = -4.5 \text{ V}, I_D = -4 \text{ A}$	Q2		41 58 58	52 78 80	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$ $V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$	Q1 Q2	20 -20			Α
<b>g</b> FS	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_D = 7 \text{ A}$ $V_{DS} = -5 \text{ V}, I_D = -5 \text{ A}$	Q1 Q2		19 11		Ø
Dynami	c Characteristics						
C <sub>iss</sub>	Input Capacitance	Q1 $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$	Q1 Q2		789 690		pF
Coss	Output Capacitance	Q2	Q1 Q2		173 306		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$	Q1 Q2		66 77		pF

#### **Electrical Characteristics** (continued) T<sub>A</sub> = 25°C unless otherwise noted **Symbol Parameter Test Conditions Type** Min Тур Max Units Switching Characteristics (Note 2) $t_{\text{d(on)}} \\$ Turn-On Delay Time Q1 Q1 2.2 4.4 ns $V_{DD} = 10 \text{ V}, I_D = 1 \text{ A},$ Q2 6.7 13.4 t<sub>r</sub> Turn-On Rise Time $V_{GS} = 10V, R_{GEN} = 6 \Omega$ Q1 7.5 15 ns Q2 9.7 19.4 Turn-Off Delay Time Q1 11.8 21.3 ns $t_{d(off)}$ $V_{DD} = -10 \text{ V}, I_{D} = -1 \text{ A},$ Q2 19.8 35.6 $t_{\rm f}$ Turn-Off Fall Time $V_{GS} = -10V, R_{GEN} = 6 \Omega$ Q1 3.7 7.4 ns 12.3 Q2 22.2 Qa Total Gate Charge Q1 16 26 nC $V_{DS} = 15 \text{ V}, I_{D} = 7 \text{ A}, V_{GS} = 10 \text{ V}$ Q2 14 23 Qgs 2.5 Gate-Source Charge Q1 nC Q2 Q2 2.4 $V_{DS} = -15 \text{ V}, I_{D} = -5 \text{ A}, V_{GS} = -10 \text{ V}$ $Q_{gd}$ Gate-Drain Charge Q1 2.6 nC Q2 4.8 **Drain-Source Diode Characteristics and Maximum Ratings** Maximum Continuous Drain-Source Diode Forward Current Q1 1.3 Α Q2 -1.3 $V_{SD}$ Drain-Source Diode Forward $V_{GS} = 0 \text{ V}, I_S = 1.3 \text{ A}$ Q1 0.74 1.2 V (Note 2)

#### Notes:

1. R<sub>8JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>8JC</sub> is guaranteed by design while R<sub>8CA</sub> is determined by the user's board design.

 $V_{GS} = 0 \text{ V}, I_{S} = -1.3 \text{ A}$ 



a) 78°/W when mounted on a 0.5 in² pad of 2 oz copper



b) 125°/W when mounted on a .02 in<sup>2</sup> pad of 2 oz copper



Q2

(Note 2)

c) 135°/W when mounted on a minimum pad.

-1.2

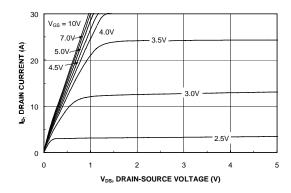
-0.76

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width <  $300\mu s$ , Duty Cycle < 2.0%

Voltage

### **Typical Characteristics: Q1**



2.4

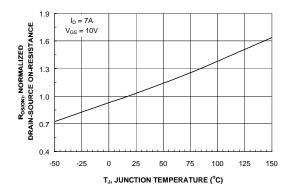
WORNALIZED

NORMALIZED

N

Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



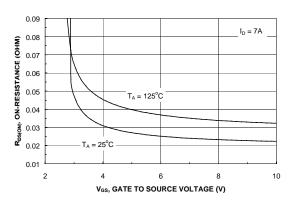
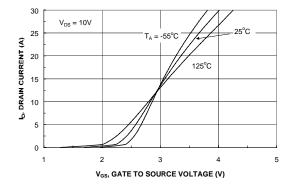


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



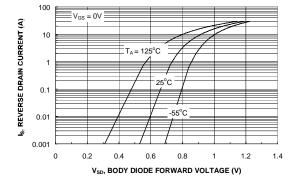
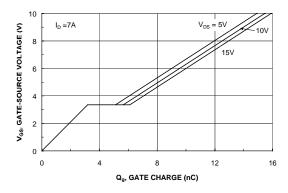


Figure 5. Transfer Characteristics.

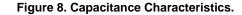
Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

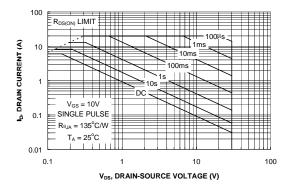
## Typical Characteristics: Q1



 $\begin{array}{c} \textbf{1200} & \textbf{f} = \textbf{1MHz} \\ \textbf{V}_{\text{GS}} = \textbf{0} \ \textbf{V} \\ \\ \textbf{900} & \textbf{C}_{\text{ISS}} \\ \\ \textbf{600} & \textbf{C}_{\text{ISS}} \\ \\ \textbf{0} & \textbf{0} & \textbf{0} & \textbf{15.0} \\ \\ \textbf{20.0} \\ \textbf{V}_{\text{DS}}, \textbf{DRAIN TO SOURCE VOLTAGE} (\textbf{V}) \\ \\ \end{array}$ 

Figure 7. Gate Charge Characteristics.





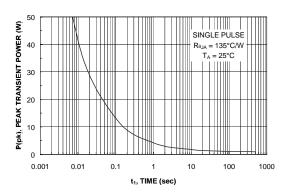


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

### **Typical Characteristics Q2**

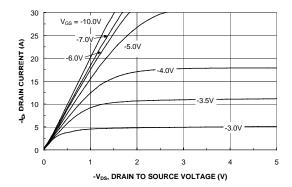


Figure 11. On-Region Characteristics.

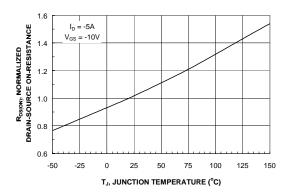


Figure 13. On-Resistance Variation with Temperature.

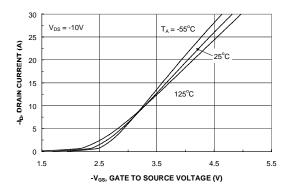


Figure 15. Transfer Characteristics.

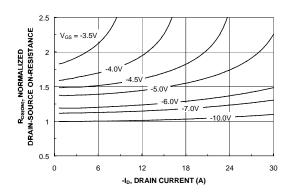


Figure 12. On-Resistance Variation with Drain Current and Gate Voltage.

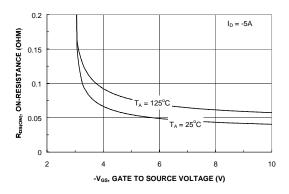


Figure 14. On-Resistance Variation with Gate-to-Source Voltage.

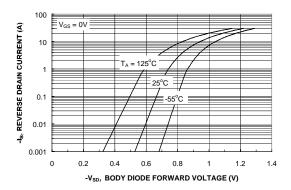
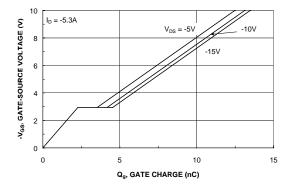


Figure 16. Body Diode Forward Voltage Variation with Source Current and Temperature.

### Typical Characteristics Q2



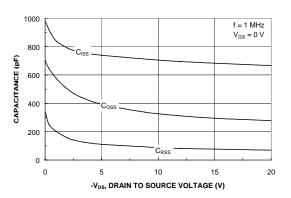


Figure 17. Gate Charge Characteristics.

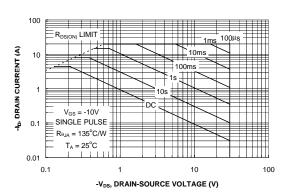


Figure 18. Capacitance Characteristics.

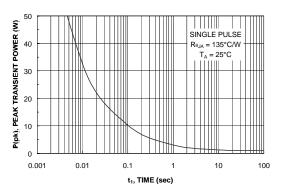


Figure 19. Maximum Safe Operating Area.



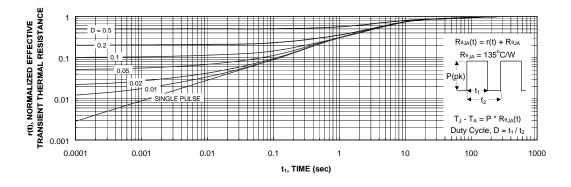
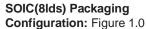


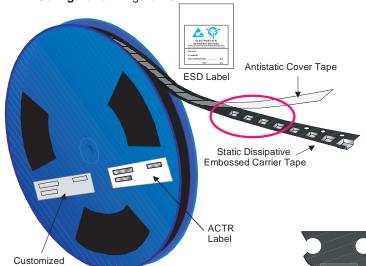
Figure 21. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

### **SOIC-8 Tape and Reel Data**

## 茂钿半導體股份有限公司 Mos-Tech Semiconductor Co.,LTD.

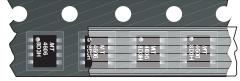




#### Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Adivated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13' or 300cm diameter real. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7' or 177cm diameter real. This and some other options are further described in the Packaging Information table.

These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.

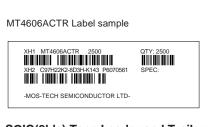


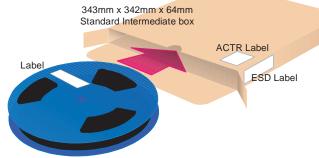


SOIC (8lds) Packaging Information Standard no flow code) **Packaging Option** L86Z F011 D84Z Rail/Tube TNR Packaging type ACTR TNR Qty per Reel/Tube/Bag 2.500 4.000 500 Reel Size 13" Dia 13" Dia 7" Dia Box Dimension (mm) 343x64x343 530x130x83 343x64x343 184x187x47 Max qty per Box 5,000 30,000 8,000 1,000 Weight per unit (gm) 0.0774 0.0774 0.0774 0.0774 Weight per Reel (kg) 0.6060 0.9696 0.1182 Note/Comments

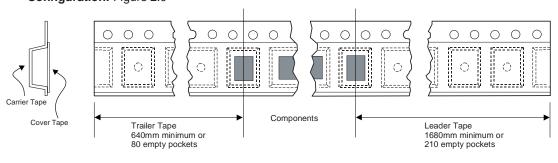
Label

**SOIC-8 Unit Orientation** 





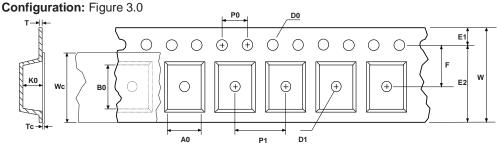
## **SOIC(8Ids) Tape Leader and Trailer Configuration:** Figure 2.0



### **SOIC-8 Tape and Reel Data, continued**



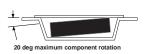
### SOIC(8lds) Embossed Carrier Tape



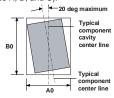


Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

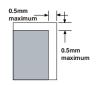


Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)

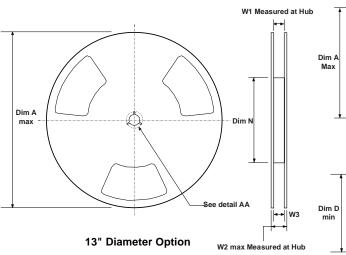
Component Rotation



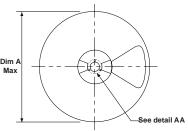
Sketch C (Top View)

Component lateral movement

#### SOIC(8lds) Reel Configuration: Figure 4.0







7" Diameter Option Dim C

							DETAIL AA	
Dimensions are in inches and millimeters								
Reel Option	Dim A	Dim A Dim B Dim C Dim D Dim N Dim W1		Dim W1	Dim W2	Dim W3 (LSL-USL)		
7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

Tape Size

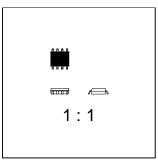
12mm

### **SOIC-8 Package Dimensions**



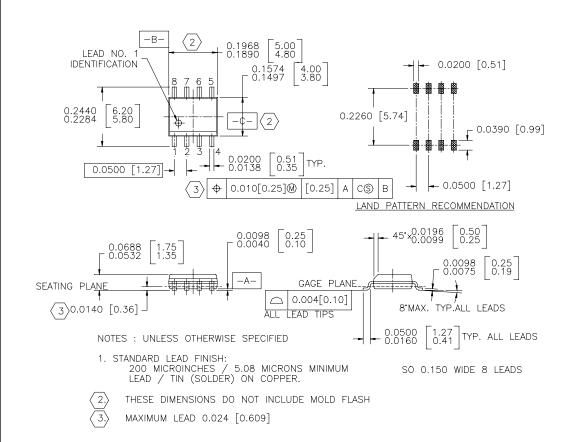
# SOIC-8 (PKG Code S1)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0774



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  - 1) 生命维持装置。
  - 2) 植埋于人体使用的装置。
  - 3) 用于治疗(切除患部、给药等)的装置。
  - 4) 其他直接影响到人的生命的装置。
- 9. 在使用本资料所记载的产品时,对于最大额定值、工作电源电压的范围、放热特性、安装条件及其他条件请在本公司规定的保证范围内使用。如果超出了本公司规定的保证范围使用时,对于由此而造成的故障和出现的事故,本公司将不承担任何责任。
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#### Keep safety first in your circuit designs!

1. MOS-TECH Semiconductor Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.